



Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- External Creepage $\geq 7.4\text{mm}$
- Distance Through Isolation $\geq 0.4\text{mm}$
- Spatial Distance $\geq 7.5\text{mm}$ (S/SL Type)
- Spatial Distance $\geq 8.0\text{mm}$ (M/SLM Type)
- Operating Temperature range - 55 °C to 110 °C
- Regulatory Approvals
 - UL - UL1577 (E364000)
 - VDE - EN60747-5-5(VDE0884-5)
 - CQC – GB4943.1, GB8898
 - IEC60065, IEC60950

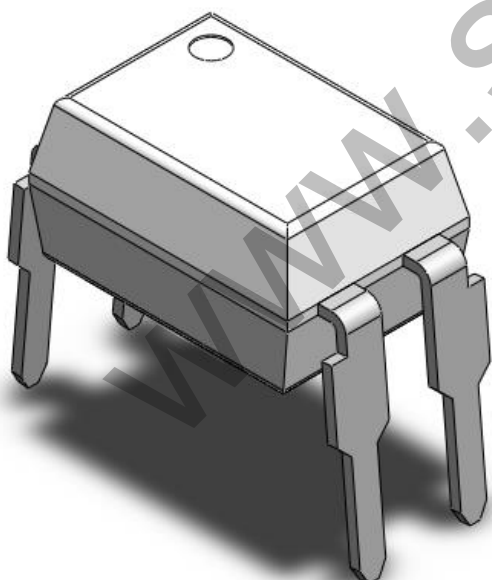
Description

The CT817 series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 4-lead DIP package different lead forming options.

Applications

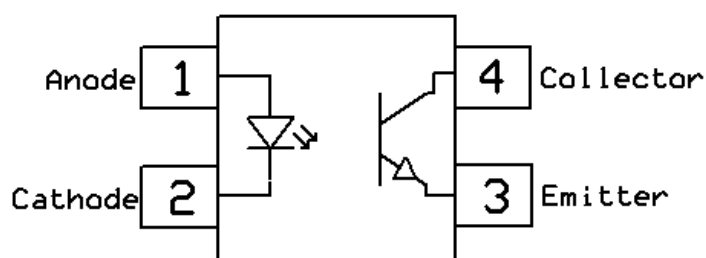
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Package Outline



Note: Different lead forming options available. See package dimension.

Schematic



**Absolute Maximum Rating at 25°C**

Symbol	Parameters	Ratings	Units	Notes
V _{ISO}	Isolation voltage (AC, 1 minute)	5000	V _{RMS}	
P _{TOT}	Total power dissipation	200	mW	
T _{OPR}	Operating temperature	-55 ~ +110	°C	
T _{STG}	Storage temperature	-55 ~ +150	°C	
T _{SOL}	Soldering temperature	260	°C	
Emitter				
I _F	Forward current	60	mA	
I _{F(TRANS)}	Peak transient current (≤1μs P.W,300pps)	1	A	
V _R	Reverse voltage	6	V	
P _D	Emitter power dissipation	100	mW	
R _{thJ-A}	Thermal Resistance Junction-Ambient	350	°C/W	
T _J	Junction temperature	125	°C	
Detector				
P _D	Detector power dissipation	150	mW	
B _{VCEO}	Collector-Emitter Breakdown Voltage	35	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	6	V	
I _C	Collector Current	50	mA	

**Electrical Characteristics** $T_A = 25^\circ\text{C}$ (unless otherwise specified)**Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V_F	Forward voltage	$I_F = 10\text{mA}$	-	1.24	1.4	V	
I_R	Reverse Current	$V_R = 6\text{V}$	-	-	5	μA	
C_{IN}	Input Capacitance	$f = 1\text{MHz}$	-	10	30	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown	$I_C = 100\mu\text{A}$	35	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown	$I_E = 100\mu\text{A}$	6	-	-	V	
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$	-	-	100	nA	

Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
CTR	Current Transfer Ratio	CT817	50	-	600	%	
		CT817A	80	-	160		
		CT817B	130	-	260		
		CT817C	200	-	400		
		CT817D	300	-	600		
	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$						
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F = 20\text{mA}, I_C = 1\text{mA}$	-	0.1	0.2	V	
R_{IO}	Isolation Resistance	$V_{IO} = 500\text{V}_{DC}$	5×10^{10}	-	-	Ω	
C_{IO}	Isolation Capacitance	$f = 1\text{MHz}$	-	0.25	1	pF	

Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
t_r	Rise Time	$I_C = 2\text{mA}, V_{CE} = 2\text{V}$	-	6	18	μs	
t_f	Fall Time	$R_L = 100\Omega$	-	8	18		



Typical Characteristic Curves

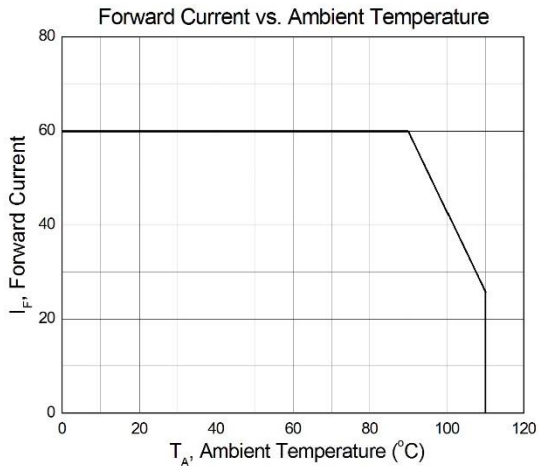


Figure 1

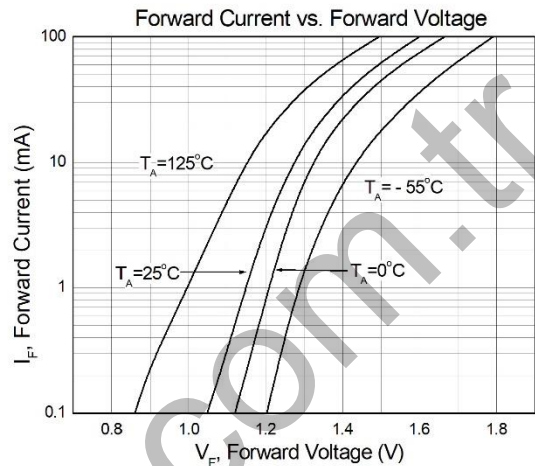


Figure 2

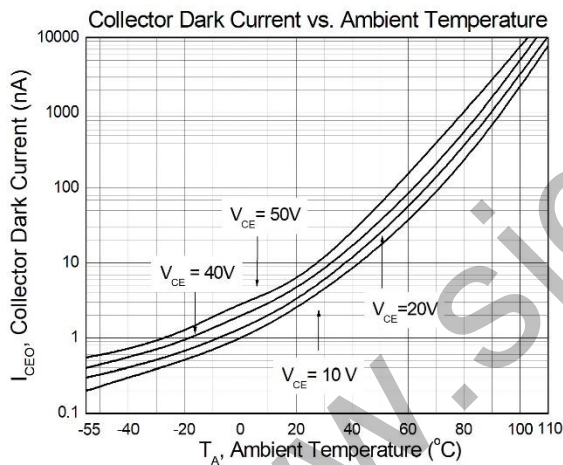


Figure 3

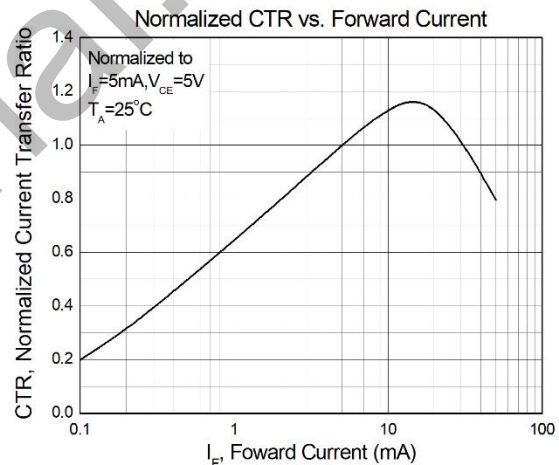


Figure 4

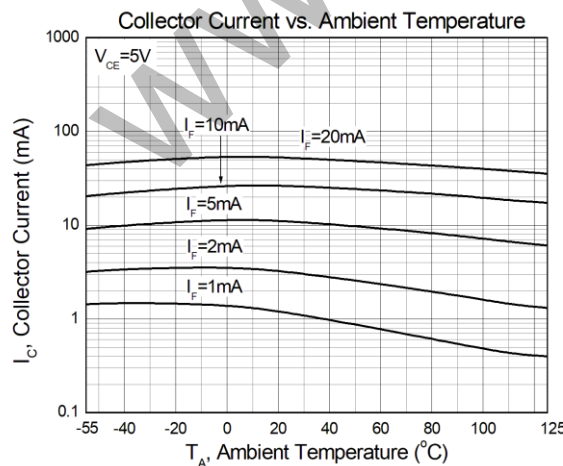


Figure 5

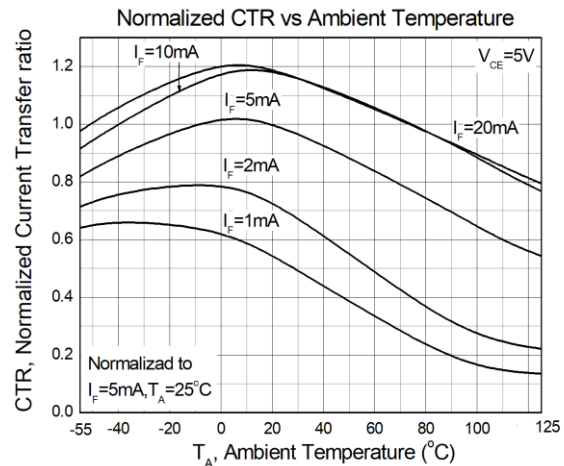


Figure 6

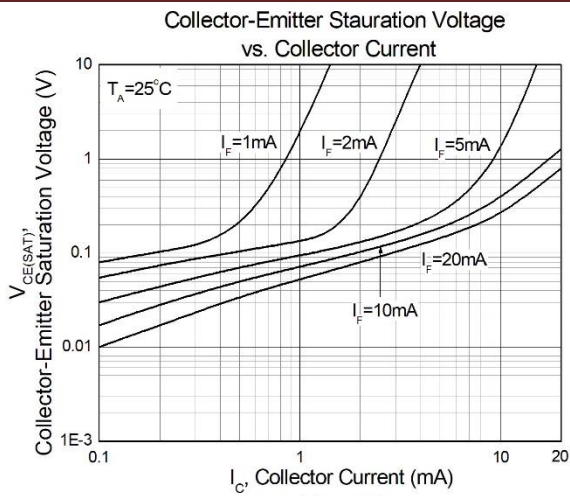


Figure 7

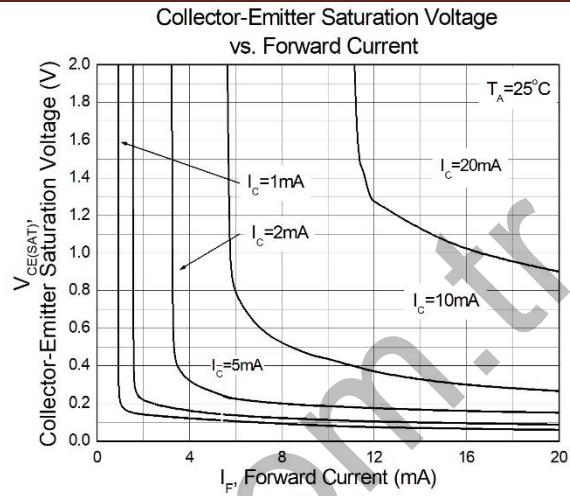


Figure 8

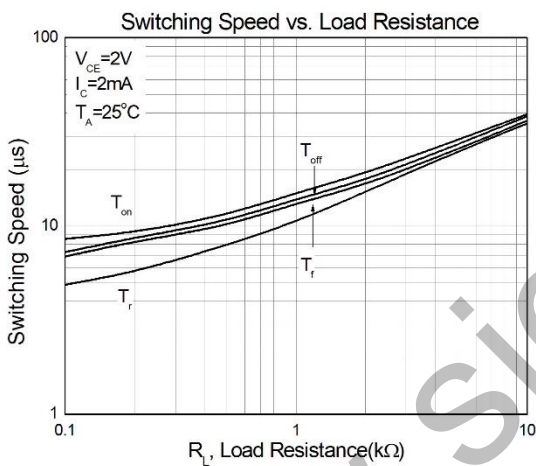


Figure 9

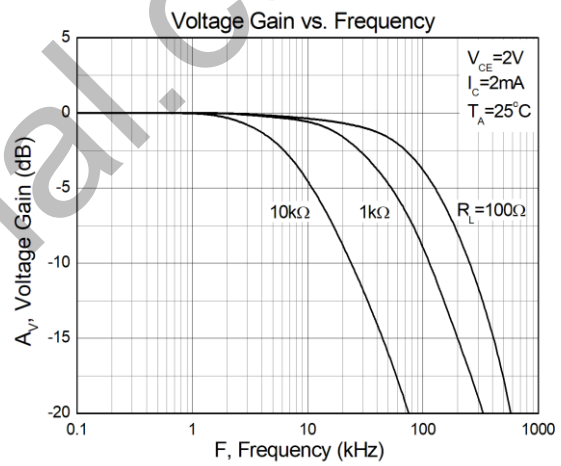


Figure 10



Test Circuit

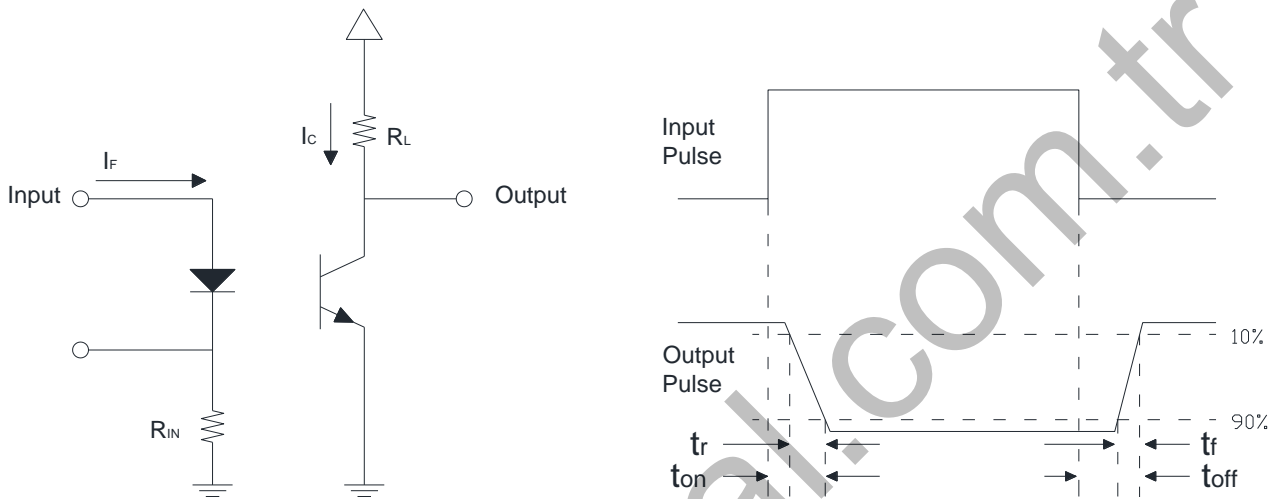
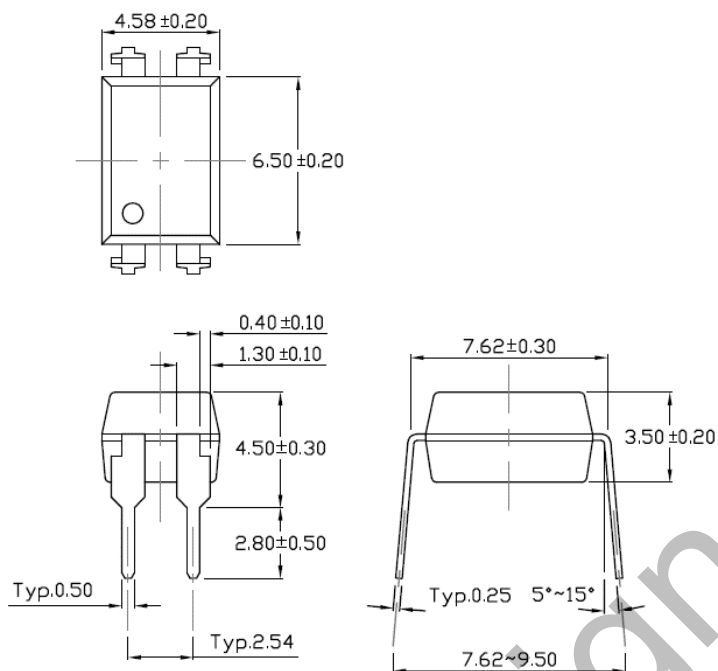


Figure 12: Switching Time Test Circuits

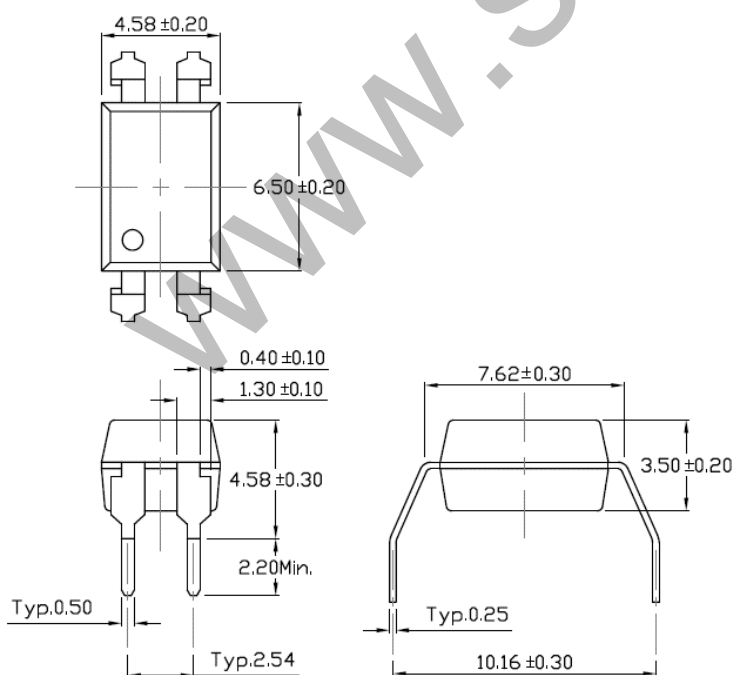


Package Dimension *Dimensions in mm unless otherwise stated*

Standard DIP – Through Hole

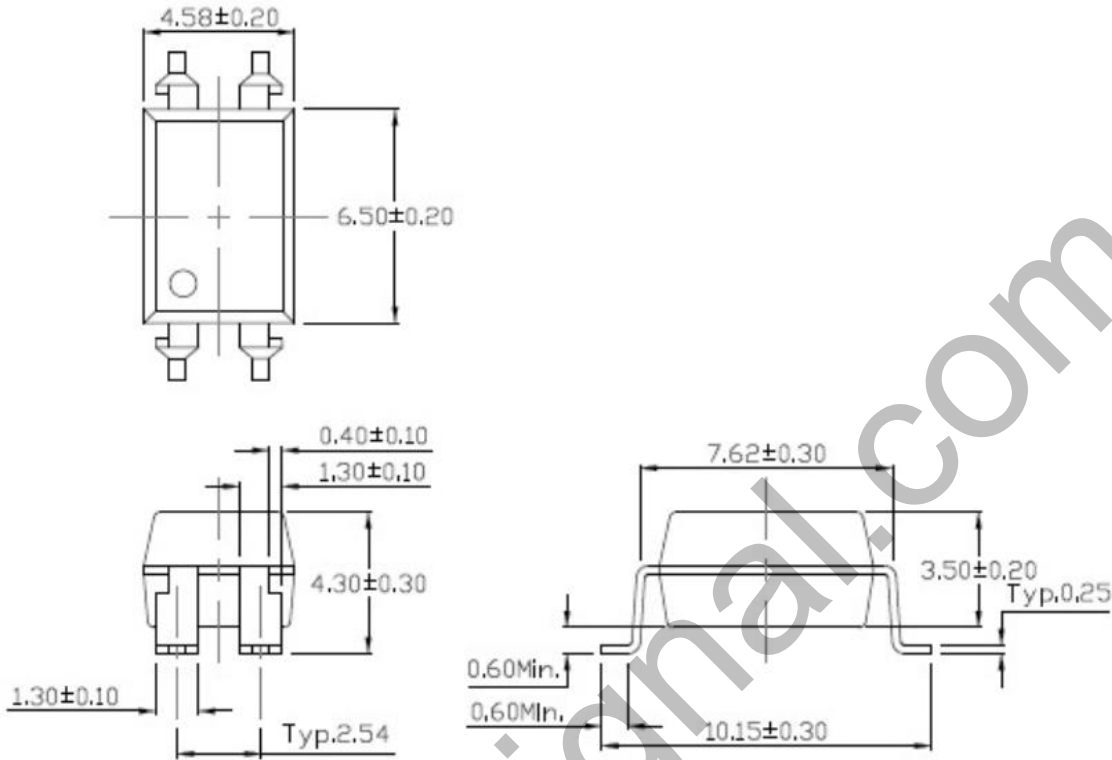


Gullwing (400mil) Lead Forming – Through Hole (M Type)

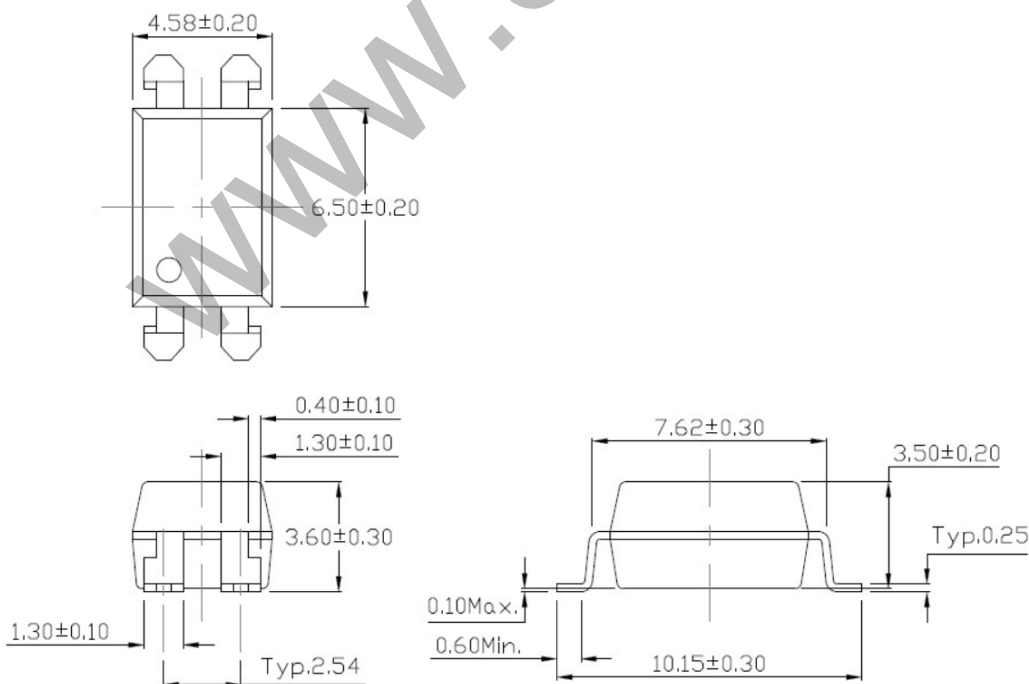




Surface Mount Lead Forming (S Type)

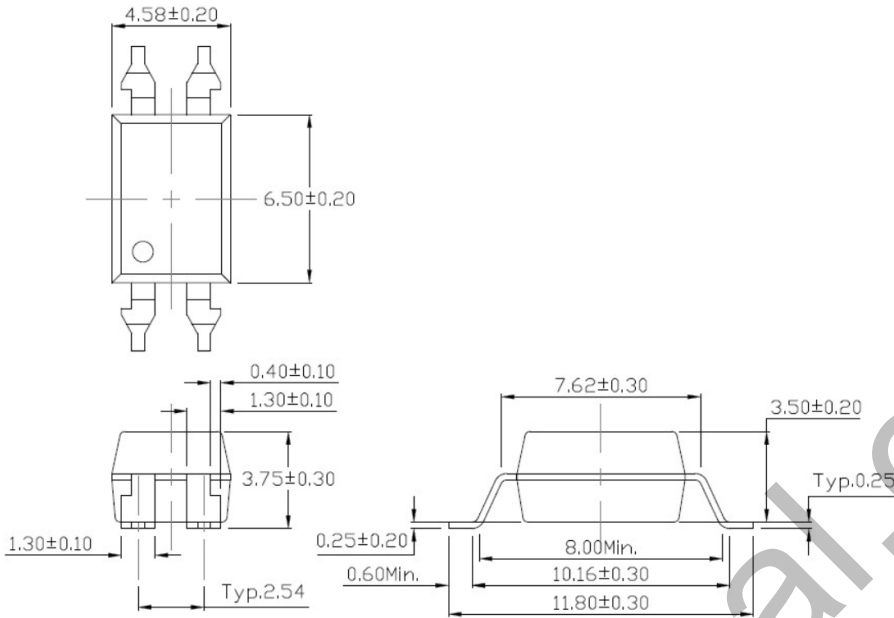


Surface Mount (Low Profile) Lead Forming (SL Type)





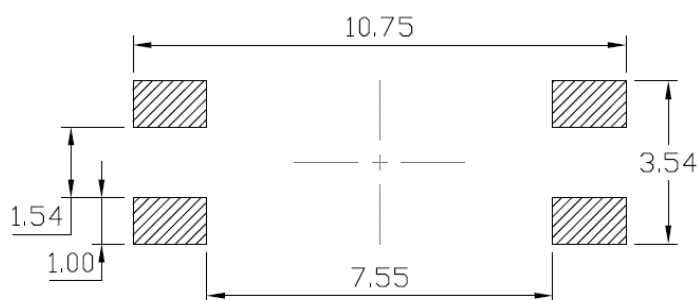
Surface Mount (Gullwing) Lead Forming (SLM Type)



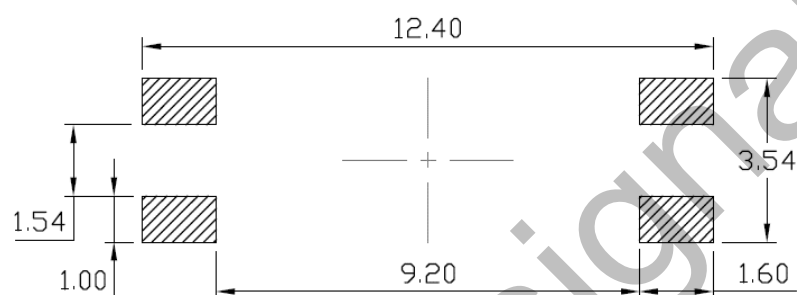


Recommended Solder Mask *Dimensions in mm unless otherwise stated*

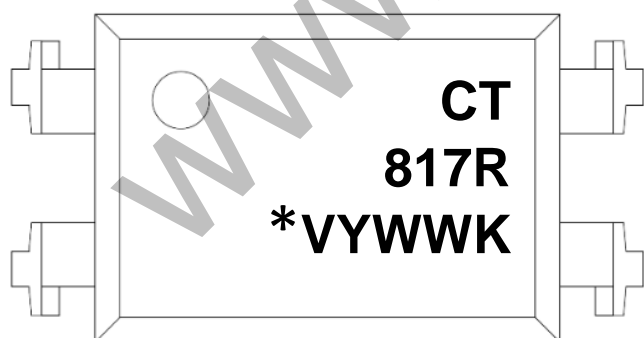
Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming



Surface Mount (Gullwing) Lead Forming



Marking Information



Note:

- CT : Denotes "CT Micro"
- 817 : Part Number
- R : CTR Rank
- V : VDE Option
- Y : Fiscal Year
- WW : Work Week
- K : Manufacturing Code

* : 第三行打 * 點為銅支架材質，不打點為鐵支架材質。

**Ordering Information****CT817X(V)(Y)(Z)-HG**

X = Part No. (X=A, B, C, D or None)

V = VDE Option (V or None)

Y = Lead form option (S, SL, M, SLM or none)

Z = Tape and reel option (T1, T2, T3, T4 or none)

H = Lead frame option (H: Iron, None: Copper)

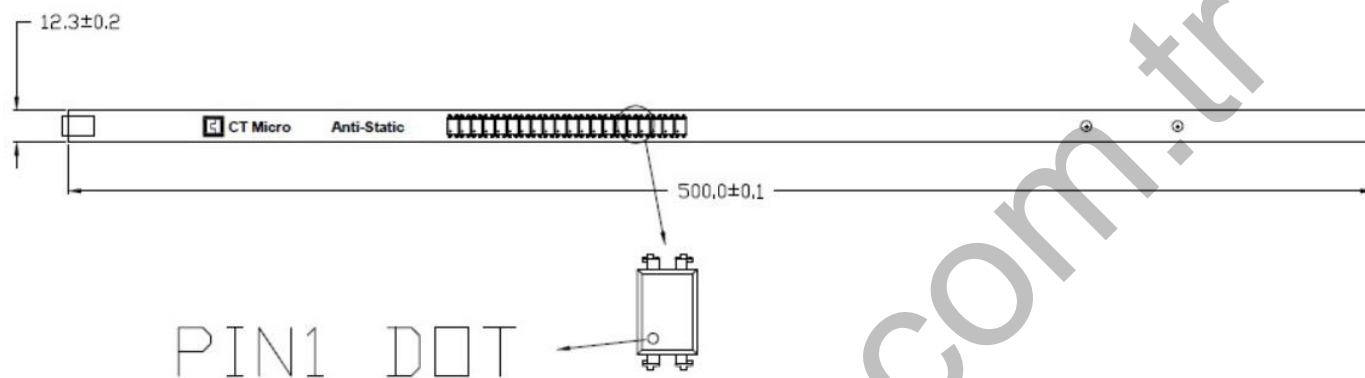
G= Material option (G: Green, None: Non-green)

Option	Description	Quantity
None	Standard 4 Pin Dip	100 Units/Tube
M	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1500 Units/Reel
S(T3)	Surface Mount Lead Forming – With Option 3 Taping	1000 Units/Reel
S(T4)	Surface Mount Lead Forming – With Option 4 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1500 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SL(T3)	Surface Mount (Low Profile) Lead Forming– With Option 3 Taping	1000 Units/Reel
SL(T4)	Surface Mount (Low Profile) Lead Forming – With Option 4 Taping	1000 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	1500 Units/Reel
SLM(T2)	Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	1500 Units/Reel

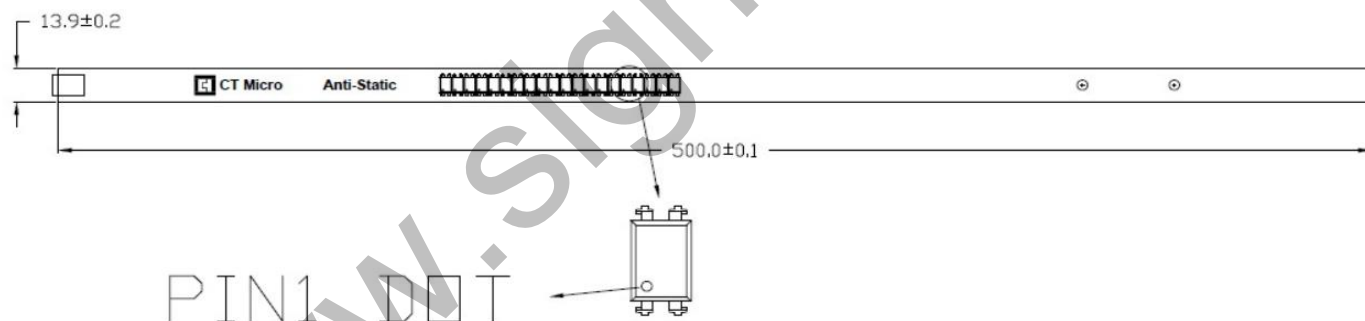


Carrier Specifications Dimensions in mm unless otherwise stated

Tube Option Standard DIP



Tube Option M Type

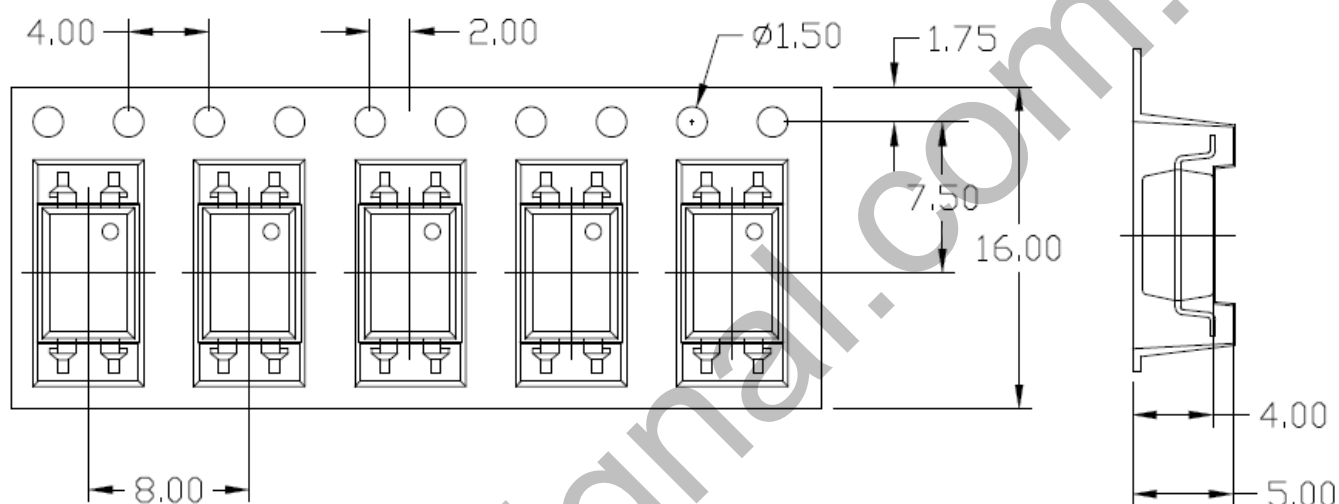




Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

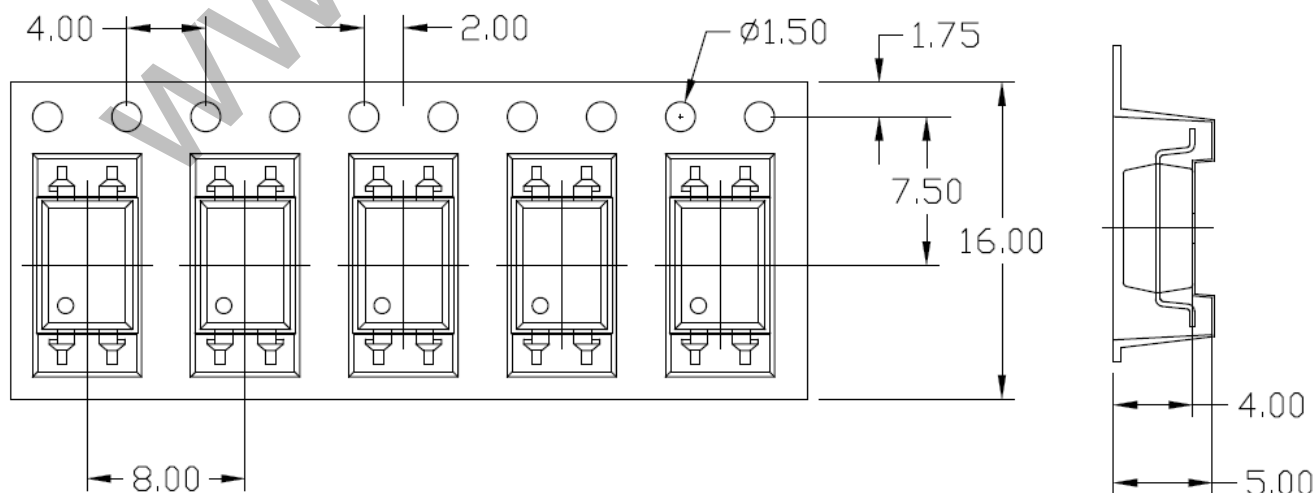
Option S(T1) & SL(T1)

Input Direction
→



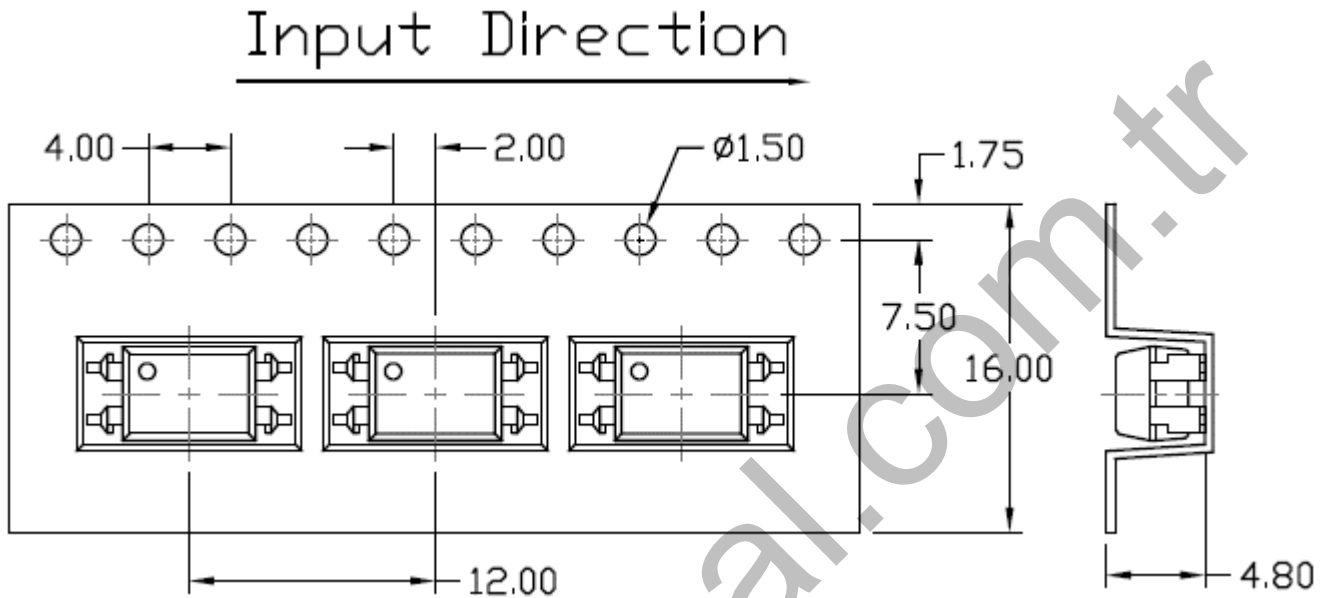
Option S(T2) & SL(T2)

Input Direction
→

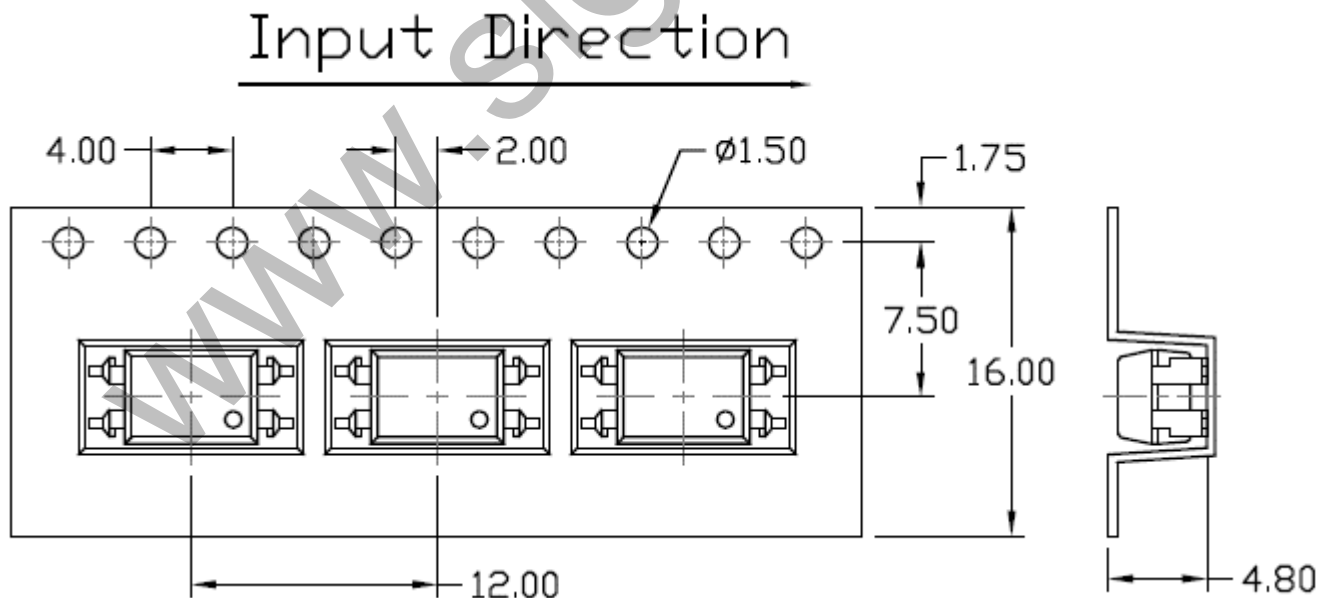




Option S(T3) & SL(T3)



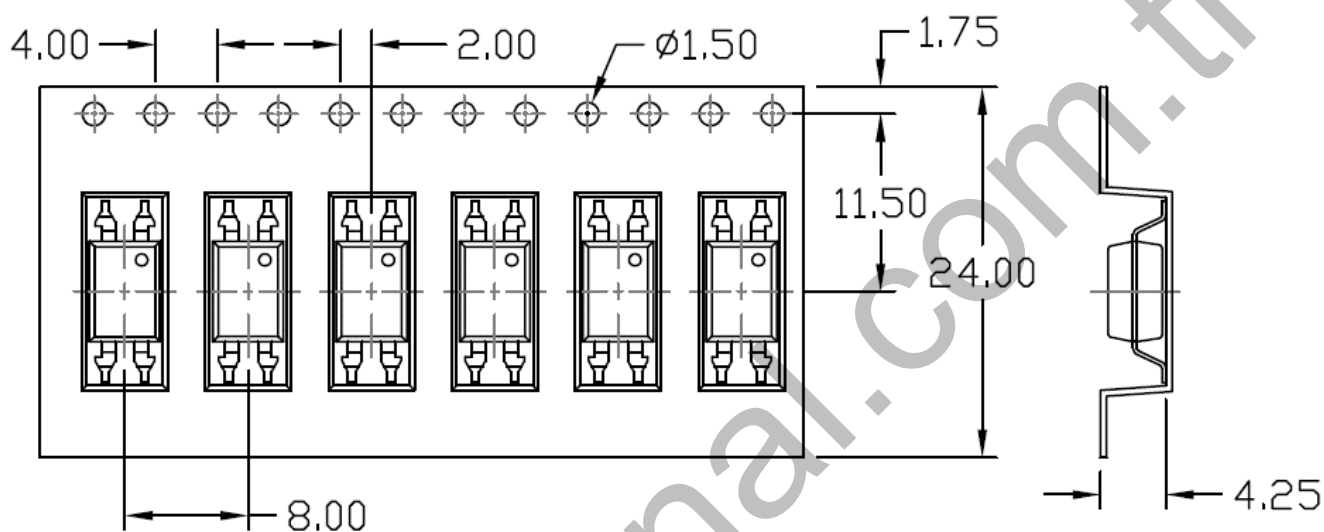
Option S(T4) & SL(T4)





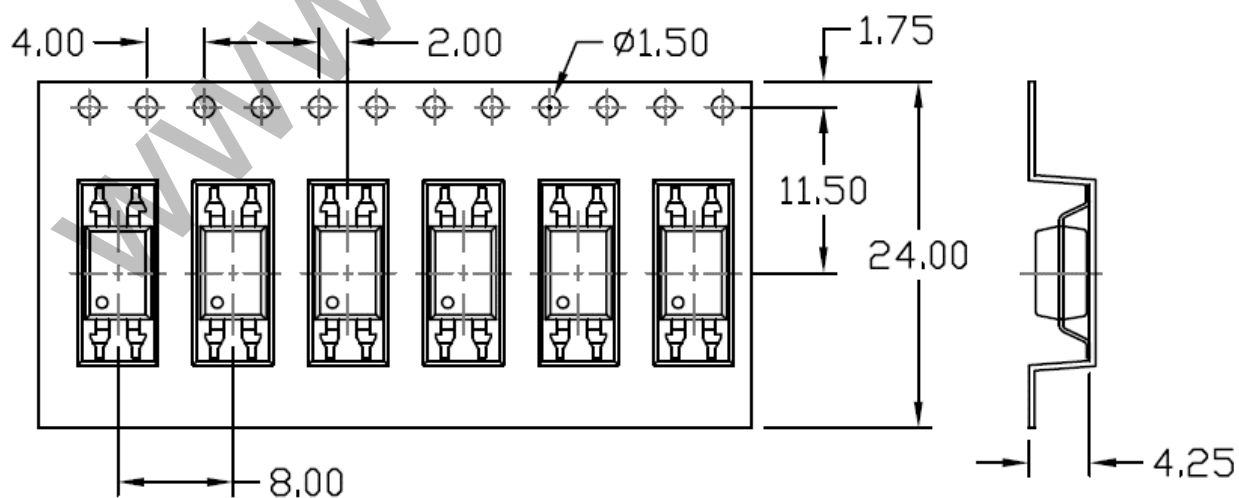
Option SLM(T1)

Input Direction



Option SLM(T2)

Input Direction



**Wave soldering (follow the JEDEC standard JESD22-A111)**

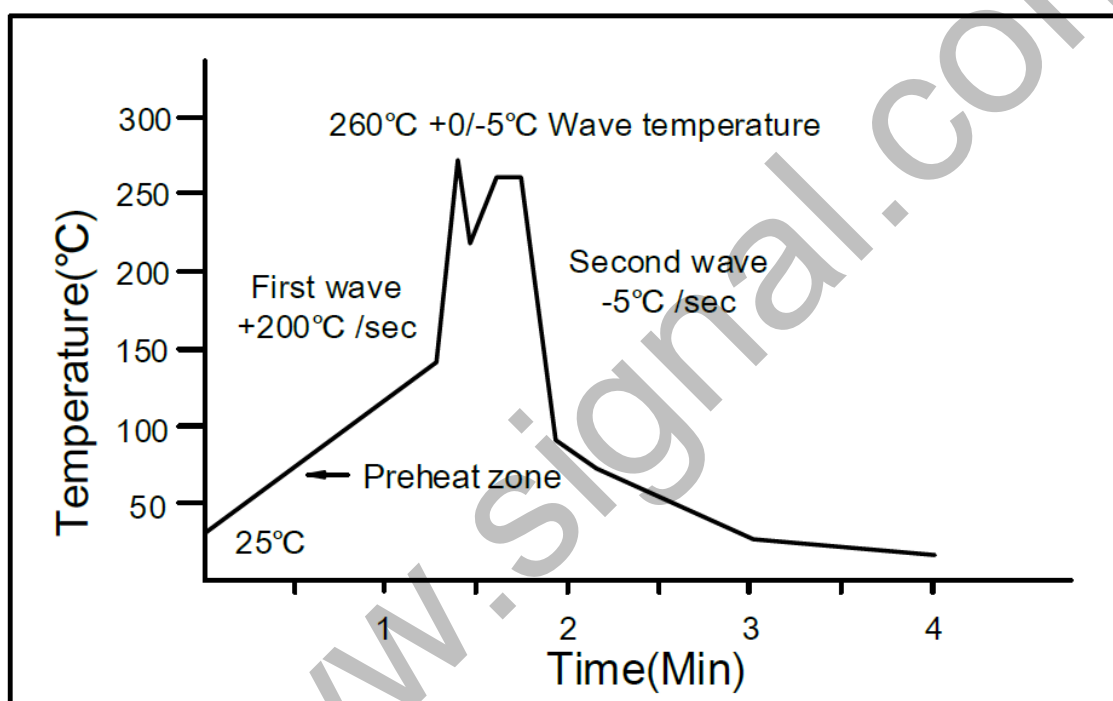
One time soldering is recommended within the condition of temperature.

Temperature: $260 \pm 5^\circ\text{C}$.

Time: 10 sec.

Preheat temperature: 25 to 140°C .

Preheat time: 30 to 80 sec.

**Iron soldering (follow the standard MIL-STD 202G, Method 210F)**

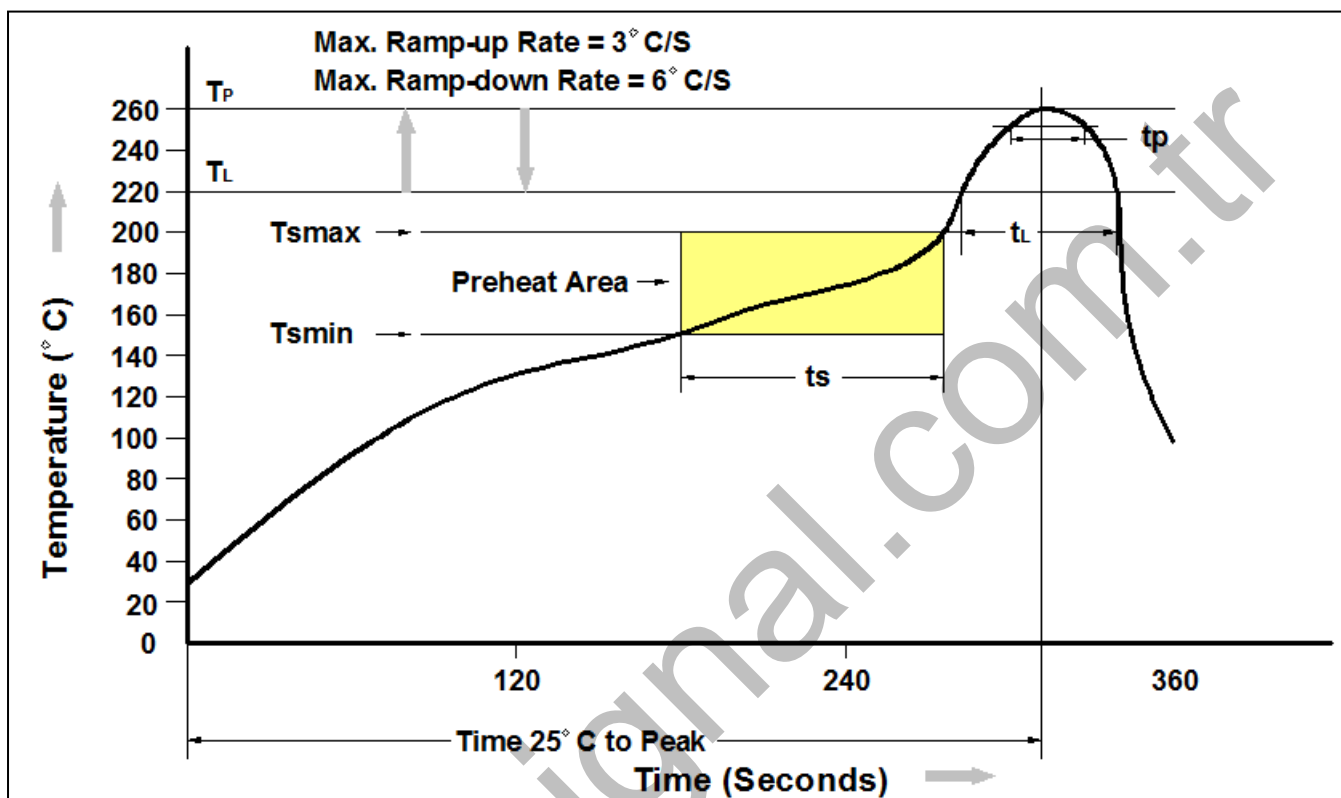
Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: $350 \pm 10^\circ\text{C}$

Time: 5 sec max.



Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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